AM4016093

Stochastic methods connected with the compilation of Fokker-Planck equations are used in this book for the first time to solve problems in structural mechanics. The end results are presented in a form convenient for use of engineering designers and scientific workers. Formulas are derived for the average and mean-square values of displacements for nonlinear and nonlinear-parametric elastic systems. Tests on models at 1/5 -- 1/6 size have confirmed the results of the theoretical research. The author is deeply grateful to R. L. Stratonovich and S. M. Targ who reviewed the manuscript and made many valuable comments, to G. A. Geniyev and M. I. Estrin for remarks concerning the manuscript, to I. I. Gol'denblat for interest in the work and advice, and to A. P. Sidorov for great help with the experiments.

TABLE OF CONTENTS [abridged]:

Foreword - - 3
Introduction - - 5
Ch. I. Motion of ideal and viscous liquids in reservoirs of different shapes - - 13

Card 2/3

AM4016093

Ch. II. Vibrations of system of n masses with cavities partially filled with water - - 23

Ch. III. Motion of partially filled reservoirs following a random disturbance - - 40

Ch. IV. Vibrations of nonlinear system - - 64

Ch. V. Vibrations of parametric system with liquid under random disturbances - - 98

Ch. VI. Experimental investigations - - 158

Appendix - - 147 Literature - - 149

SUB CODE: IB, MM

SUBMITTED: 08Nay63

NO REF SOV: 109

OTHER: 031

DATE ACQ: 10

1000063

Card 3/3

VCRCHTSOV, N.M.; GUNER, J.V.; NIKOLAYENKO, N.A.; SEMEYEROV, S. Ya., Amed. tekhn. nauk; GOVGR, U.S.

Rolls for rolling lightweight channels. Sbor. trud. UNIDA no.9:196-216 164 (MIRA 18:1)

EPR/EMP(j)/T/EMP Pe-5/Pf-4/Rr-4/P	//EMT(d)/EPA(s)-2/EWT(m)/i (t)/EWP(k)/EWP(h)/EPA(bb)-2 so4/Pt-7/Pab IJP(c) JD/	/ewp(z)/ewp(b)/ewp(1)/ewa(w/ww/em/rm	h)/EWA(1) 40 Pc-4/
AM5013205	BOOK EXPLOITATION		001.24:536.4
		UEL: 739.4.	or. 541 220.4
Bezukhov, N. 1 - Technical Sc	L: Bazhanov, V. L.; Go ciences; Professor); Ni	Co; 16, I. I. (Doc kolayenko, N. A.; Sin	or of yukov, A. M.
Calculations o	of <u>strength</u> , stability,	and vibrations under	high tem-
peratureVcon	nditions ((Raschety na p v usloviyakh vysokikh t	rochnost, ustoychivo	at I
"Mashinostro	oyeniye" 1965. 0566 p.	illus., biblio. Er	rata slip
TOPIC TAGS: a vibration, t stress	structure strength; str thermal elasticity, the	acture stability, str rmal plasticity, cree	ucture p thermal
and scientiff of higher te the theory of stability, a	OVERAGE: This book is fic workers. It may also chrical education as a fit thermal stresses. Mand vibration of structures to large high-terms.	so be used by students supplementary text for the street of calculating area used in machine-	or studying the strength, building
Card1/6			

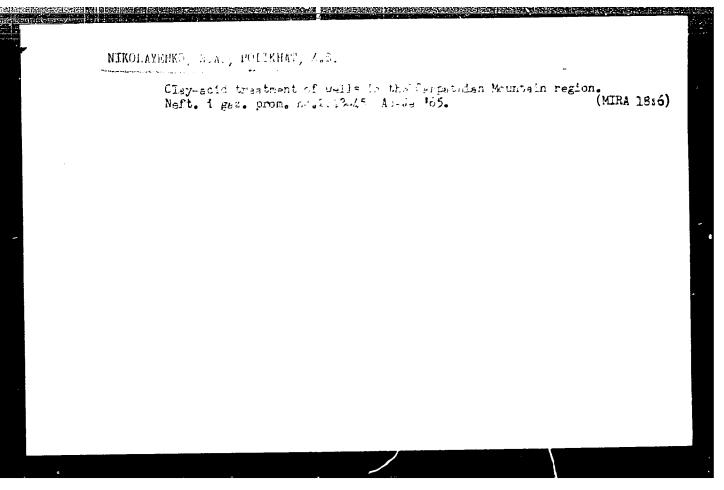
L 55159-6	교환하다. 교육하는 지난 발생님, 그런 나는 아는	
M501320	: 회장은 화를 받는 전 하면도 하는 전 보험 전 전환 전 전환 이번을 보고 가장은 상황에 하는 전 회장은 하는 경험이다. 상태를 하고 한 화를 보고 하는 것 같아. 되는 것 같아.	
PABLE O	F CONTENTS (Abridged):	
Forewor	d3	
Basic S	ymbol s 5	
Introdu	otion == 7	清
	PART I. THERMOMECHANICAL PROPERTIES OF MATERIALS. THERMAL REGIONS	
	General Characteristics of Thermomechanical Properties of Structural Materials and Acceptable Stresses 10	
Ch. 2.	Review of Methods for Calculating Thermal Regions in Element of Structures 43	58
215110	graphy 65	

L 55159-65 AM501320	(数数) 医多数分子的 医皮肤 医皮肤 医皮肤 医皮肤 医皮肤 医皮肤 化二甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基甲基	
	PART II. BASIC EQUATIONS OF THERMAL ELASTICITY, PLASTICITY AND CREEP	
Oh. III.	Basic Equations of Thermal Elasticity - 66 Basil Equations of Thermal Plasticity and Creep 102	
	Certain Special Problems of the General Theory of Thermal	
cn. v.	Stresses and Deformations 115	
	PART III. NONUNIFORMLY HEATED PLATES AND TURBINE BLADES	
Ch. VI.	Round Plates and Turbine Blades 135	
	Rectangular Plates 228	
	PART IV. NONUNIFORMLY HEATED THIN-WALL ROTATION SHELLS	

55159-65 AM5013205	1,75	
Ch. VIII. Axisymmetrical Elastic Deformation of Nonuniform! Heated Thin-Wall Rotation Shells 262	y	
Ch. IX. Slanting Tapered and Spherical Shells 295		
Ch. X. Nonuniformly Heated Thin-Wall Shells Operating in the Region of Elastic-Plastic Deformations 336	e	
Ch. XI. Inelastic Stability of Nonuniformly Heated Ring and Oylindrical Shell 364		
PART V. THERMAL STRESSES IN CERTAIN SPECIAL TYPES OF STRUCTURES		
Ch. XII. Thermal Stresses in Special Shaft-Type Structures	 3 96.	
Ch. XIII. Thermal Stresses in Principal Structures of Nucle	ar	
Reactors 41		
Ch. XIV. Nonuniformly Heated Thick-Wall Shells 433		

L 55159-65		
AM5013205		6
Ch. XV. Cer	tain Dynamic Problems of Thermal Klasticit	y 487
Bibliography	사람은 생활하다면서 경험을 가는 중에 하면도 가지가 되었다. 하면 가게 되었다는 것이 되었다는 것은 얼마나 아들이 되었다. 그리고 있다는 것이 없었다.	
Appendices -		
Table of uni	ts used in the book converted into interne	itional
	Carbon steel 501	
	Structural alloy steels 518 4	
Appendix 3.		
Appendix 4.	Aluminum alloys 530	
Appendix 5.	Magnesium wrought and cast alloys 544	
Appendix 6.	Titanium alloys 549	

L 55159-65 AM5013205 Appendix 7. Piper-gla	s reinforced	plastics	553 es:		
Appendix 8, Hyperboli Bibliography 561 SUB CODE: MM, IE OTHER: 679	c circumferent			gov: 276	



LOSKUTOVA, Ye.A.; NIKOLAYENKO, N.F.

Effect of neural factors on the thyroid function of rats of various ages. Probl. endok. i gorm. 6 no. 4:24-28 J1-Ag '60.

(MIRA 14:1)

(THYROID GLAND) (AGING) (NERVOUS SYSTEM)

NIKOLAYENKO, N.F.

Changes in the absorption of radioactive iodine by the thyroid gland during potassium perchlorate therapy and during its combination with the use of 6-methylthiouracil. Probl. endok. i gorm. 6 no. 4:102-106 Jl-Ag '60. (MIRA 14:1) (POTASSIUM PERCHLORATE) (URACIL) (HYPERTHYROIDISM) (IODINE METABOLISM)

NIKOLAYENKO, N.F.

Change in the absorption of radioactive iodine by the thyroid gland during prolonged 6-methylthiouracil therapy. Frobl. endok. i gorm. (MTRA 14:1) 6 no. 5:39-44 '60.

(HYPERTHYROIDISM) (IODINE METABOLISM)

BARANOV, V.G.; BLAGOSKLONNAYA, Ya.V.; NIKOLAYENKO, N.F.

Relation between neuroses and thyrotoxicosis. Terap.arkh. 32 no.12:24-29 160. (MIRA 14:2)

1. Iz laboratorii vozrastnoy fiziologii i patologii cheloveka (zev. - deystvitel'nyy chlen AMN SSSR prof. V.G. Baranov) Instituta fiziologii imeni I.P. Pavlova AN SSSR. (NEUROSES) (HYPERTHYROIDISM)

Combined treatment of patients with toxic goiter by methylthiouracil and radiactive iodine (I-131). Klin.med. 38 no.7:73-78 160. (MIRA 13:12) (HYPERTHYROIDISM) (URACIL) (IODINE-ISOTOPES)

MIYCLAYPYKC, ". F.

Dissertation defe ded at the Institute of Physiology imeni I. F. Favlov for the academic degree of Candidate of Undical Science:

"Dynamics of Radioactive Iodine Absorption by the Thyroid Glan' in the Process of Extender Treatment with Methylthicuracil and Combination Treatment with Methylthicuracil and Radioactive Iodine with Patients of Toxic Coiter."

Vestnik Akad Mauk, No. 4, 163, pp. 110-145

NIKOLAYEVA, V.V.; NIKOLAYENKO, N.F.

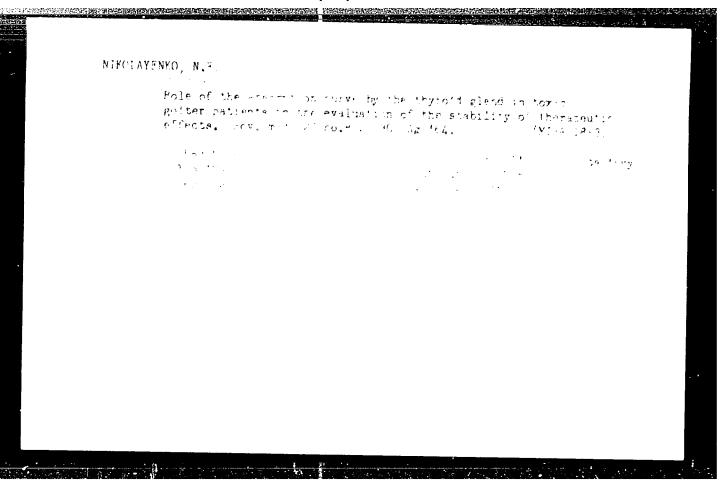
Cortical influences on thyroid function in experimental neurosis in dogs. Zh. vyssh. nerv. deiat. Pavlov 13 no.3: 530-536 '63. (MIRA 17:9)

1. Laboratorii kortiko-vistseral'noy patologii i vozrastnoy fiziologii i patologii cheloveka Instituta fiziologii im.

I.P. Pavlova Akademii nauk SSSR.

(NEUROSES) (THYROID FUNCTION TESTS)

(IODINE ISOTOPES, DIAGNOSTIC)

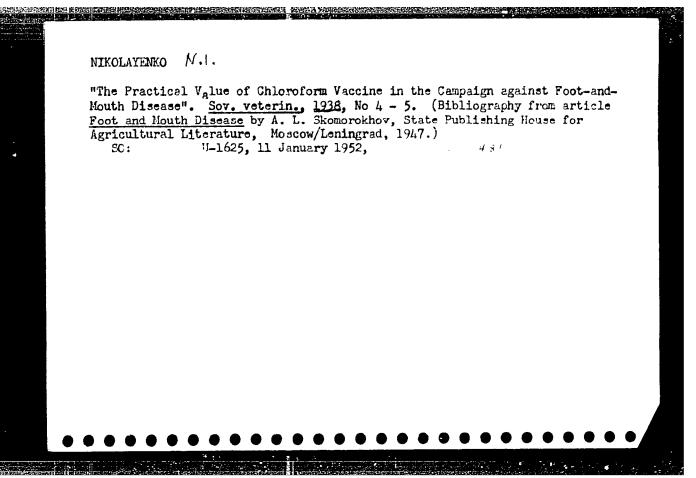


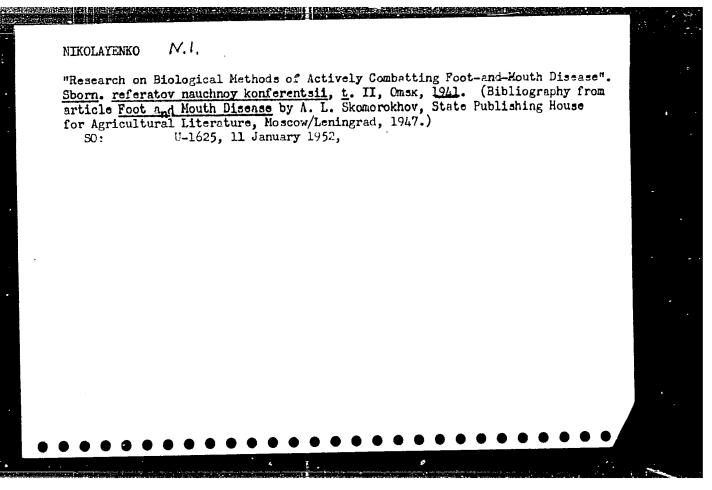
BARANCY, V.G.; NIKCLAYFREG, N.F.; STEPANCY, G.S.

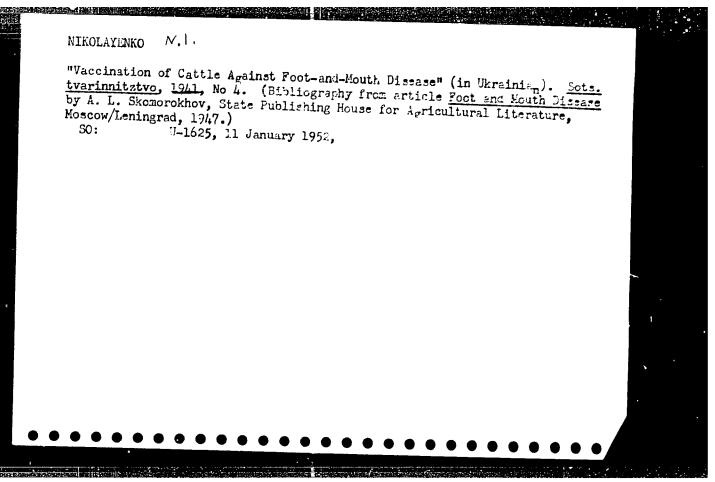
Treatment of diffuse toxic goiter with potarsium perchlorate combined with reservine. Frobl. endok. i gorm. 11 nc.1:3-9

Ja-F 165. (MIRA 18:5)

l. Laboratoriya vozrastnov filologii i patologii endokrinnov sistemy cheloveka (zav. - ;ref. V.G. Baranov) Instituta fiziologii imeni Favlova (dir. - akademik V.N. Chernigovskiy, AN SSSR i kafedra endokrinologii (zav. - prof. V.G. Baranova Instituta usoverskenstvovaniya vrachey imeni Kirova, Leningrad.







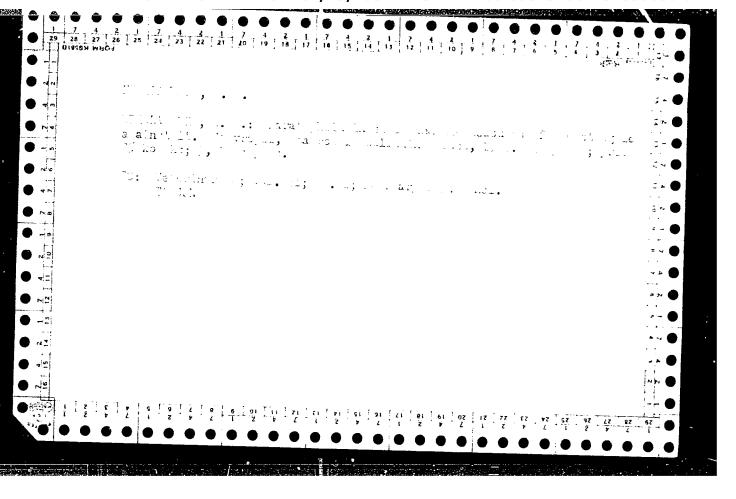
USSR/Medicine - Paratyphoid Jun 50
Sheep, Diseases

"Paratyphoid of Sheep and Measures of Controlling It," Prof N. I. Nikolayenko, Stavropol' Agr Inst, A. I. Nefed'yev, Dr Vet Med, Stavropol' Biologicals Plant, 1½ pp

"Veterinariya" No 6

Tests virulence of strains of B. paratyphi abortus ovis on sheep and results of various methods of vaccination on resistance of sheep to the disease.

161783



USSR / Diseases of Farm Animals. Diseases Caused ty Bacteria and Fungi.

R-1

Abs Jour: Ref Zhur-Biol., No 2, 1958, 7307

: N. I Nikolayenko Author

: Concerning the Prophylaxis of Paratyphoid of Sheep Inst Title

Orig Pub: Tr. Stavropolisk. s-kh. in-ta., 1956, vyp. 7, 299-

306.

Abstract: A verification of the effectiveness of the formolaluminous microbe anatoxin deposited vaccine, prepared from the strains of Salmonella ovis, showed that a two stage administration of the vaccine protects from infection 70.8 percent of the lambs vaccinated at the 6-30 day age, and 73.9 percent of the nursing ewed On farms, having cases of paratyphoid, the author recommends the vaccina-

Card 1/2

15

NIKOLAYENKO, N.I., prof.

[Bacter.al fertilizers]_mayterial'nye usebrenila.
Stavropol', Stavropol'skoe knizhnoe izd-vo, 1944.

(M.M.A. Fr.:

1. Stavropol'skiy sel'skokhozyaystvennyy institut.

BUSHUYEV, V.P.; GUBIN, G.V.; GONCHARENKO, Yu.I.; KARMAZIN, V.I.;

MARGULIS, V.S.; MITROV, V.A.; NIKOLAYENKO, N.O.; BOBRUSHKIN, L.G.;

BUROV, A.I.; RYBAKOV, V.N.; SOSHIN, A.F.; TATSIYENKO, P.A.;

TOVSTANOVSKIY, O.D.; YUROV, P.P.; Prinimali uchastiye:

NIFAGINA, A.A.; CHERNYY, I.I.; GERSHOYG, Yu.G.; KOSTIKOV, A.G.;

DOLGIKH, M.A.; MOVSKOVICH, S.A.; STUPIN, D.D.; NEVOYSA, G.G.

Magnetization roasting of Kerch ores in the experimental factory of Kamysh-Burun Combine. Gor. zhur. no.12:30-37 (MIRA 15:11)

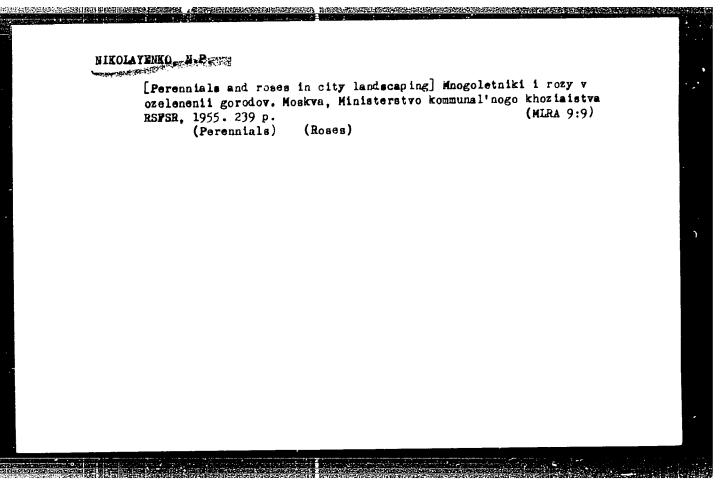
1. Institut Mekhanobrchermet, Krivoy Rog (for Bushuyev, Gubin, Goncharenko, Karmazin, Margulis, Mitrov, Nikolayenko, Nifagina, Chernyy, Gershoyg, Kostikov). 2. Kamyshburunskiy zhelezorudnyy kombinat, Kerch' (for Bobrushkin, Burov, Rybakov, Soshin, Tatsiyenko, Tovstanovskiy, Yurov, Dolgikh, M.A.; Movskovich, S.A.; Stupin, D.D.; Revoysa).

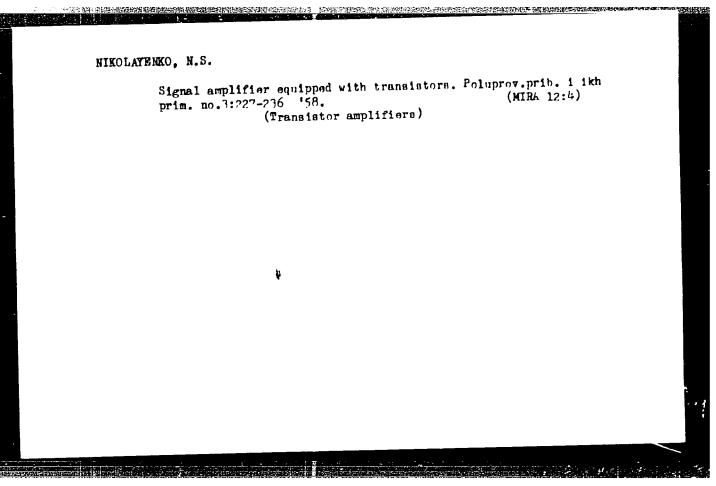
(Kerch Peninsula—Ore dressing)

MIKOLAYNING, N. P. - "The effect the formula of the ovaries of material plants are a the biological and decorative indications of the second paterity." The substitution (Akad. kommunal. khoz.-ve in. artitov., Is to 1, 1, 9, 1, 12-2).

SO: U-1030, 21 Cct. 3, (Letonis 'Zhurnol 'myke St. tey, No. 1., 1-27.

NIKOLÁZNKO, N. P.	ė.
Cultivation practices for growing ornamental clants in urban floriculture establishments Moskva, Ministerstvo kommunalinogo khoziaistva, 1950. 235 p.	
	!
	72.58





HIKOLAYENKO, N.S.; KALLIOPIN, G.V.

Amplifier with output connected to a reversible motor.
Poluprov.prib. i ikh prim. no.3:237-246 '58. (MIRA 12:4)
(Transistor amplifiers)

sov/108-13-2-2/15

AUTHOR:

Mikolajenko, M. S.

TITLE:

Direct-coupled Triode Transistor Amplifiers

(Usilitel na poluprovodnikovykh triodakh s neposredstvennoy

svyaz'yu)

PERIODICAL:

Radiotekhnika, 1950, 701. 13, Nr 2. pp. 14 - 22 (USSR)

Received: April 25, 1958

ABSTRACT:

The work carried out here showed that r transistor alternating current amplifier with galvanic intercascade connection can be produced, which is better with respect to the temperature than the ordinary amplifiers. Moreover many details are omitted here as transition condensers or transformers, base resistances for all cascades except the first. This increases the reliability of the scheme and in the case of broad-band or high-frequency amplifiers it improves the parameters of the scheme. The statements are demonstrated by means of a scheme. The alternation of cascades with common point in the emitter and collector permits to obtain a better temperature stabilization and a good conformity between the cascades, which on the other hand offers the possibility to

Card 1/4

SOV/108-13-2-2/15

Direct-coupled Triode Transistor Amplifiers

obtain a sufficient power amplification, even under application of transistors of average quality. The temperature stabilization of the whole amplifier is determined by the stabilization of the first cascade and a correct alternation of the semiconductor triodes in the scheme, if these show different values of the zero-collector-current. The advantages of this very simple scheme with a minimum number of particulars are shown. The scheme makes possible to produce transistor amplifiers, which are capable of working up to a tempera ture of 100°C of the surrounding medium. - A calculation of the method of operation of the scheme is given. The values of the constant amperages and voltages are computed, which determine the method of operation and the temperature modifications of these values. At first the first cascade is investigated without considering the following cascades and it is shown that for a better temperature stabilization the low-resistance divider of R, and R, as well as of the highly resistive resistance R, in the emitter circuit are necessary. The total value of the input resistance is ally determined by the load current. Then the suggested three-cascade scheme (as a whole) is investigated. It is shown that the influence

Card 2/4

SOV/108-13-2-2/15

Direct-coupled Triode Transistor Amplifiers

of the third cascade on the first can be neglected. The equation (38) for the temperature dependence of the collector voltage in the first triode and thus also of the operation of the emitters on the following cascades is derived. Equation (38) shows that the decrease of the collector voltage together with the temperature in the suggested scheme is always smaller than in an individual carcade, that is, with the same parameters. The computation shows that an amplican very easily be projected fier with direct coupling for the operation within a large temperature range. Then the computation of the power amplifier, beginning with the third cascade, is given. Summarily it is ascertained that the necessary quantity of the collector voltage of the following cascades can be obtained by lowering the load resistance, lowering the emitter amperage by inserting the divider in the preceding cascade (the basis of the respective cascade is connected to the center of load of which) and by a successive increase of the supply voltage from cascade to cascade. Such amplifiers have been constructed by the

Card 3/4

Direct-coupled Tricks frameistor Amplifiers.

Author and are in operation, languager J. 7. Kalingian and Engineer Ye. I. 2hdanova participated in the work. There are 8 figures, and 1 Soviet reference

SUBMITTED: July 8, 1957

Card 4/4

NIKOLAYENKU, N.S.

66209

SOV/146-59-1-4/21

0(2) 9,2520

AUTHORS:

Tanskiy, Ye.A., Candidate of Technical Sciences, Docent, and

Nikolayenko, N.S., Senior Engineer

TITLE:

A Servo System With a Transistorized Amplifier

PERIODICAL:

Izvestiya vysshikh uchebnykh zavedeniy, Priborostroyeniye, 1959,

Nr 1, pp 28-33 (USSE)

ABSTRACT:

The authors describe a servo system with a transistorized ac amplifier. The circuit diagram is shown in fig.l. The amplifier has two stages. One PIG and two P3V transistors are used. DG-T324 diodes are used as voltage limiters. The power amplification is about 53 db. The amplification factor at the outlet is around 400. The arrangement of the parts in the assembled amplifier is shown in fig.5. The experimental data on the frequency characteristic coincide with theoretical data. The efficiency of the output stage is about 60%. The transistors are installed for cooling purposes on aluminum radiators having a surface of 15 cm². The amplifier was built at the Kafedra avtomatical it telemekhaniki (Department of Automation and Remote Con-

Card 1/2

S0V/120-59-2-40/50 Bogomolov, V.N., Nikolajerko, N.S. and Fedotov, V.P. AUTHORS:

A D.C.-A.C. Convertor Based on the Use of the Hall Effect TITLE:

(Preobrazovatel' postoyannego toka v peremennyy,

osnovannyy na ispolizovanii effekta Kholla)

PERIODICAL: Pribory i tekhnika eksperimenta, 1959, Nr 2.

pp 134-135 (USSR)

THE PARTY OF THE RESIDENCE PROPERTY OF THE PARTY OF THE P

ABSTRACT: A cross-section through the device is in Fig 1. It is 40 mm in diameter and 40 mm high and consists of a permalloy screen surrounding a toroidal work with a KhVP core. The coil is designed to annept 50 //s at

6.3 V and draws 0.1 A. The power dissipation is 0.2 W. The semi-conductor wafer (5 x 3.5 x 0.3 mm3) of n-type 8 ohm om germanium is secured by epoxy resin in an air gap in the core. It has an imput resistance of 100 obms

and an output resistance of 500 oims. The surrent conversion ratio DC-AC is 20%. The effective flux density is 15000 gauss. The voltage transfer moefficient

is 1.2-1.3 per 1000 gauss of field. A compensating coil is also included, as in Fig 2, to increase sensitivity and thermal stability. The converter is intended for

operation with the EPP-09 recording potentiometer. Card 1/2 systematic and random compenents of error are both 0,2%

SUV/120-59-2-40/50 A D.C.-A.C. Converter Based on the Use of the Hall Effect and the sensitivity is 5 micro watts. The temperature coefficient is 0.01 % per degree centigrade and the sensitivity falls with temperature. The converter is insensitive to ± 10% change in supply voltage, ± 5% change in supply frequency and the effects of moisture. It is suggested that the unit find application as a computing element or in a d.c. amplifier. V.I. Pogodir. is thanked for his assistance. Card 2/2 There are 2 figures.

ASSOCIATION: Institut poluprovodnikov AN SSSR

(Semiconductor Institute of the Ac. Sc. USSR)

SUBMITTED: April 5, 1958

NIKOLAYENKO. N.S. aspirant	
Some circuits of semiconductor phase-sensitive devices. Izv.vys. ucheb.zav.; prib. 2 no.5:20-25 '59. (MIRA 13:5)	
 Leningradskiy elektrotekhnicheskiy institut imeni V.I. Ul'yanova (Lenina). Rekomendovana kafedroy elektroizmeritel'noy tekhniki. (Transistors) 	

67463

SOV/146-2-4-1/19

9(4)-9.4310

Aspirant Nikolayenko, N.S.,

AUTHOR: TITLE:

Semiconductor Transistor in a Phase-Sensitive System

PERIODICAL:

Izvestiya vysshikh uchebnykh zavedeniy. Priboro-

stroyeniye, 1959, Nr 4, pp 3-11 (USSR)

ABSTRACT:

This is a theoretical and experimental investigation of a semiconductor junction-type germanium transistor of the "p-n-p" type, trade mark "PI", in a phasesensitive system whose principal circuit diagram is shown in figure 1. The working principle is described, and the experimental results are illustrated in graphs (Figure 2,3,4,5,6), showing the different relationships of the amplification coefficient of Due to this research, a series of the transistor. instruments on semiconfrictor transistors was developed, among them signal amplifiers, amplifiers with a connection to a relay, etc., all these instrume to

Card 1/2

67463

307/146-2-4-1/13

Semiconductor Transtistor in a Phase-Sensitive System

were described previously by the author /Reference 1 7. This article was recommended by the Kafedra elektroizmeritel'noy tekhniki (The Chair of Electro-Measuring Technique). There are 1 diagram, 5 sets of graphs,

and 1 Soviet reference.

ASSOCIATION: Leningradskiy elektrotekhnicheskiy institut imeni V.I. Ul'yanova /Lenina/ (Leningrad Electrical Engineering Institute imeni V.I. Ul'yanov /Lenin/).

SUBMITTED:

April 14, 1959

STREET, STREET,

Card 2/2

9(3,2)

SOV/146-2-5-3/19

AUTHOR:

Nikolayenko, N.S., Post-Greduate Student

TITLE:

Some Semi-Conducting Phase-Sensitive Devices

PERIODICAL:

Izvestiya vysshikh uchebnykh zavedeniy. Priboro-

stroyeniye, 1959, Nr 5, pp 20 - 25 (USSR)

ABSTRACT:

The working principles and design calculations of phase-sensitive devices with semiconductor diodes and triodes are discussed. The following circuits, are investigated: the single-cycle phase-sensitive electrovacuum triode circuit (Figure 1); the two-cycle half-wave phase-sensitive circuit (Figure 2);

the transformer load phase-sensitive circuit (Figure 2) the transformer load phase-sensitive circuit (Figure 4); the amplification cascade circuit fed by a pulsating current (Figure 5). The output circuits of all these phase-sensitive systems are fed by alternating current as mentioned previously by the author / Ref 1 / . It is concluded that

Card 1/2

the calculation formulae for phase-sensitive cas-

SOV/146=7-5-3/19

Some Semi-Conducting Phase-Sensitive Devices

THE THE PART OF THE PROPERTY OF THE PROPERTY OF THE PARTY OF THE PARTY

cades are in close agreement with experimental results, and can therefore, be used for engineering purposes. All the circuits of phase-sensitive systems listed were applied in different instruments, e.g. signal amplifiers, relay output amplifiers, amplifiers with output to a reversible motor, phase-sensitive translators, etc This article was recommended by the Kafedra elektroizmeritel'noy tekhniki (the Chair of Electro-Metering Technique). There are 4 diagrams, 1 graph, and 1 Soviet reference.

ASSOCIATION: Leningradskiy elektrotekhnicheskiy institut imeni V.I. Ul'yanova/Lenina (The Leningrad Electrical

Engineering Institute imeni V.I. Ul yarav/Lenir)

SUBMITTED:

July 7, 1959

Card 2/2

9(2)

S/146/59/002/06/003/016 D002/D006

AUTHOR:

Nikolayenko, N.S., Engineer

TITLE:

Semi-Conductor Phase-Sensitive Amplifiers With Relay

Output

PERIODICAL:

Izvestiya vysshikh uchebnykh zavedeniy. Priborostroy-

eniye, 1959, Nr 6, pp 17-22 (USSR)

ABSTRACT:

The author gives design and performance information on two amplifiers: 1) An amplifier with an "RP-4" relay output (Figure 1 and 2, circuit diagram and photograph) working on 127 volt ac net (± 10%), 50 cycles (±5%) and at a temperature range of the surrounding medium of -30 - +60°C; it has a sensitivity of 0.5 millivolt at a transmitter resistance of approximately 1 kiloohm, consists of 3 cascades with transformer connection built on "P13" low-power

triodes. 2) An amplifier (Figure 5) with electro-

Card 1/2

APPROVED FOR RELEASE: 07/19/2001 CIA-RDP86-00513R001137030008-8"

S/146/59/002/06/003/016 DOO2/DOO6

Semi-Conductor Phase-Sensitive Amplifiers With Relay Output

magnetic relay output with a power of up to 3 watts; it works on the same voltage and frequency as the first amplifier in a temperature range of the surrounding medium of 0 to 50°C. Its performance was checked with the "RKN" relay which has a coil resistance of 220 ohms, and with the "MKU-48" relay which has a coil resistance of 320 ohms. Sensitivity with the "MKU-48" relay was 6 millivolts, and with the "RKN" 4 millivolts, and depended on the change of the surrounding temperature. The article was recommended by the Kafedra elektroizmeritelinoy tekhniki (Chair of Electrical Measurement Technology). There are 2 diagrams, 1 photograph, 2 graphs and 2 Soviet references.

ASSOCIATION:

Leningradskiy elektrotekhnicheskiy institut ımeni V. I. Ul'yanova/Lenina (Leningrad Electrotechnical In-

stitute imeni V.I. Ul'yanov/Lenin) November 24, 1959

SUBMITTED:

Card 2/2

9(4)

SOV/119-59-3-2/19

AUTHORS:

Andreyev, A. A., Engineer, Nikolayenko, H. S., Engineer

TITLE:

Semiconductor Amplifiers for Automatic Measuring Devices

PERIODICAL: Priborostroyeniye, 1959, Nr 9, pp 6-8 (USSR)

ABSTRACT:

In circuits of automation and control technique semiconductor diodes and triodes practically always replace vacuum tubes. Investigations made in the design office showed the possibility of using a scheme with direct coupling. In this connection the theoretical and experimental advantages of this type of circuit with inductance and capacity coupling were proved. In extension of work in this direction the design office developed amplifiers for automatic devices the output of which is connected to a reversive motor. These amplifiers have a simple and elegant circuit arrangement, and are highly sensitive and reliable in operation. To begin with, semiconductor amplifiers for alternating current were discussed. This apparatus is intended for use in automatic equipment, which measures physical parameters transformed into a.c.-signals. Apparatus of this type are, e.g. automatic bridges, potentiometers for a.c., induction instruments, etc. The amplifiers are suitable for Geiger-instruments

Card 1/3

point in the property of the control of the co

THE CHIEF STREET STREET, WHEN THE WORLD STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET, STREET,

SOV/119-5/-9-2/19

and for recorders of all the calibrations provided by the GOST (All-Union State Standard). The circuit diagram of the amplifier is illustrated in a figure. The amplifier consists of 6 cascades. The authors then describe certain details of the circuit arrangement. The problem of stabilizing the temperature in circuits with direct coupling had been solved previously. The correctness of these deductions was proven experimentally for a circuit consisting of 5 cascades. The input amplifier was calculated by means of graphical-analytical methods. The sensitivity of the amplifier was controlled by means of an alternating-current resistance interconnected between the emitter and the base of the triode of the third cascade. The output cascade was also calculated by graphical-analytical methods, and its efficiency amounted to 70%. Thus semiconductor triodes were applicable down to stray power of less than 1 w. The amplifier in question had a sensitivity threshold of approximately 1 microwatt at an input resistance of around 1,000 ohm. Thus an electric power of 10^{-15} w enters the amplifier. Apparatus equipped with specimens of this amplifier fit well into the 0.5 class. The semiconductor amplifier is

Card 2/3

Semiconductor Amplifiers for Automatic Measuring Devices

SOV/119-59-9-2/19

adapted for operation in a surrounding medium at 0 - 60° . performance being most dependable when maintained constantly in a medium at 60° C. The tests carried out in a factory gave good results. No trouble during operation has been experienced hitherto. The second part of the paper deals with a semiconductor amplifier for direct current, which is intended for use in automatic potentiometers and in d.c. bridges. It is distinguished from the above amplifier by containing a small size electromechanical oscillation transformer. The circuit diagram of the automatic recording potentiometer is given in a figure. This semiconductor amplifier is composed of miniatur wireless parts, and contains miniature transformers, which were developed and produced in the design office. The semiconductor amplifier surpasses electronic amplifiers concerning all parameters. Besides, semiconductor amplifiers are ready for use practically immediately. At present the design office is testing a semiconductor amplifier having a feed back concerning speed, which is adapted for use in automatic recorders. The laboratory tests gave good results. There are 3 figures and 1 table.

Card 3/3

S/194/61/000/011/061/070 D271/D302

AUTHOR:

Nikolayenko, M.S.

TITLE:

Types of feedback in transistor amplifiers

PERIODICAL:

Referativnyy zhurnal. Avtomatika i radioelektronika. no. 11, 1961, 14, abstract 11 K106 (V sb. Poluprovodnik. pribory i ikh primeneniye, no. 6, 11., Sov. ra-

dio, 1960, 235-253)

TEXT: A graphical method is proposed for designing low-frequency transistor amplifiers with feedback; the method is based on two transistor parameters; current gain K; andinput resistance Rin in the common emitter circuit. The parameters are functions of the collector and load currents and fully describe the amplification properties of transistors. Various types of feedback are considered: Series, parallel, combined, selective and non-linear, as well as current and voltage limiters. Non-linear semiconductor resistances and semiconductor diodes are considered as non-linear elements. The

Card 1/2

S/194/61/000/011/001/070
Types of feedback...

methodology of design and application of limiters is italicated.
Results of experimental checking of formulae and their validity limits are shown. Abstracter's note: Complete translation.

Card 2/2

S/119/60/000/011/007/009 B012/B054

9.6000 (1067,1099,1159)

Nikolayenko, N. S. and Shapqshnikov, V. B.

TITLE:

AUTHORS:

Scaling Device Made From Semiconductor Triodes for the

Integrator

PERIODICAL: Priborostroyeniye, 1960, No. 11, pp. 18 - 20

TEXT: The authors describe a phase-sensitive device with semiconductor triodes which can be used as scaler in a thermometric integrator. The mode of operation of the integrator is based on the successive summation of time spaces which are proportional to the temperature measured at each point of time. The said device with semiconductor triodes serves for amplifying and transforming the a.c. signal. The phase of this signal corresponds to the position in which the signal taken up by the synchronously rotating rheochord, and compared with the signal proportional at the respective moment of the object temperature, is weaker than the reference signal. The difference signal with a frequency of 50 cycles is transformed to impulses with 1.56 cycles. These impulses are fixed when the relay responds. The relay operates the mechanical counter which works Card 1/5

Scaling Device Made From Semiconductor Triodes for the Integrator

S/119/60/000/011/007/009 B012/B054

at an input signal of a certain phase. The number of impulses is proportional to the amount of heat. The present device is intended for temperatures of the medium between 0 and 50°C. Fluctuations of the feeding voltage amount to $\pm 10\%$, those of the frequency to $\pm 5\%$; they do not affect the work of the device. The threshold of sensitiveness is 10 μ v. It is pointed out that it is possible to construct an integrator with a minimum number of contacts and very small dimensions with the aid of semiconductor diodes and triodes. The cost of such a device is, however, very high (synchronous motor!) as compared with usual scaling devices. The figure shows the basic circuit diagram of the device, and the table the rated values of resistors and capacitors. The power preamplifier consists of five stages. At its input, there is a transformer with a transformation ratio of 1:1. The circuit scheme of the amplifier is similar to that described in Ref. 1. The graphical-analytical method of Ref. 2 was used to calculate the power amplification factor. The amplification factor is 100 db. The input signal amplified by the preamplifier passes over an intermediate transformer to the phase-sensitive stage, and then to the formation stage where rectangular impulses are formed. The formed impulse then reaches the input of the 5-cell scaling circuit, each cell being a Card 2/5

Scaling Device Made From Semiconductor Triodes for the Integrator

S/119/60/000/011/007/009 B012/B054

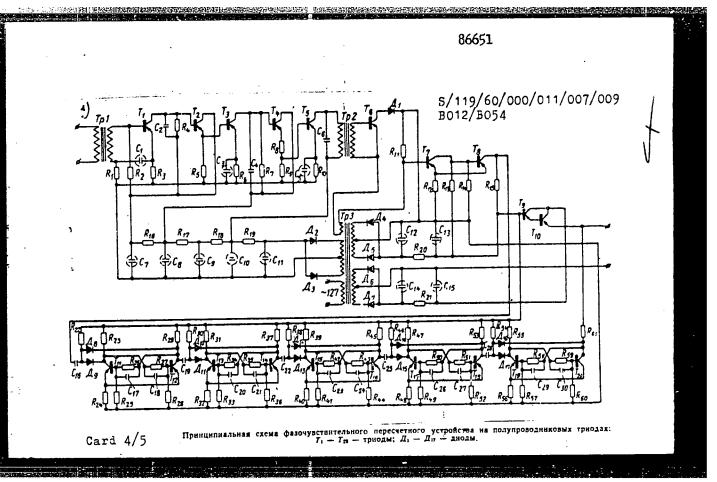
trigger with two stable positions. A model of the circuit described was made and tested. The test showed that the device guarantees perfect and reliable work; if the production cost could be reduced it would be widely used. There are 1 figure, 1 table, and 5 Soviet references.

Legend to the figure: Basic circuit diagram of the phase-sensitive device with semiconductor triodes; T_1 - T_{20} triodes, $H_1(D_1)$ - $H_{17}(D_{17})$ diodes.

1) Transformer.

Legend to the table: Rated values of resistors and capacitors: 1) Resistor, 2) value of resistance in kiloohms, 3) capacitor, 4) value of capacitor in microfarads, 5) value of capacitor in picofarads, 6) Note. All resistors are of the 9.7 (ULM) type; the capacitors C₂, 4, 6 are of the 6.7 (MBM) type; the capacitors C₁, 3, 5, 7, 9, 10, 11, 12, 13, 14, 15 of the 3.7 (ETO) type, and the capacitors C₁₆₋₃₀ of the 5.4 (BM) type.

Card 3/5



Powinianthind Shevening Conparations of Comparations (Constraint) (Con								ANA.	E723			YEL Y						7	
Comportuaziente Shavening Conportinaziente no vontreace properties Comportuaziente Comportuazien			-	,	į ·												86651		
Номинальные значения сопротивления (в. 12. 21. 22. 40. 48. 58 0,51 С2 Ro. 13 (в. 12. 21. 22. 40. 48. 58 0,51 С2 Ro. 13 (в. 12. 21. 22. 40. 48. 58 0,51 С2 Ro. 13 (в. 13. 15. 22. 23. 31. 37. 33 0 С3. 7 (в. 13. 15. 23. 23. 31. 37. 33 0 С3. 7 (в. 13. 15. 23. 23. 31. 37. 33 0 С3. 7 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 23. 33. 35. 41. 44. 49. 22 75.0 С16-33 (в. 21. 24. 24. 24. 25. 24. 25. 25. 25. 25. 25. 25. 25. 25. 25. 25	енсаторов	Значенне конденса.	0,1	0,5	15,0	20,0	30,0	50,0	80,0			995		<u> </u>		S B	5/119/60/000/011/0 B012/B054	07/009	
HOMINIAJENIME 3HAVEILING 4) Comportuatente Res 12. 21. 22. 40. 48. 58 Res 13. 21. 23. 40. 48. 58 Res 13. 35. 51. 31. 37. 33 Res 47. 53. 55. 61 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53 Res 27. 34. 35. 42. 43. 50. 51. 58. 53				C4. 6	C ₁₀ 11	4. 4.	C ₁ , 8		Cs			8,910] Thina <i>YAM</i> ; kon Period ide ide ide				
HOMMINAJENINE 3HAVEHING 4) Comportuatente Res 12. 21. 22. 40. 48. 58 Res 13. 21. 22. 40. 48. 58 Res 15. 21. 22. 31. 37. 33 Res 47. 53. 55. 61 Res 27. 34. 35. 42. 43. 50. 51. 58. 58 Res 26. 34. 35. 42. 43. 50. 51. 58. 58 Res 30. 38. 46. 54 Res 30. 38. 46. 54 6) If p in a b e h in e. Bee con Control and a b of the boundary o	E ::	Энвчение сопротив». В виняя	16,0	1,0	1,5	2,4	3,0	3,0	1'9	12,0	[_ [75,0	0,001	TOTHBACIUM Cum to m		· · · • · · · · · · · · · · · · · · · ·		
	Номинальные значения	\$	21. 22, 40. 48.	R10- 19	R ₁₁	3, 16, 17, 15, 20,	13, 15, 23, 29, 31, 37,	47, 53, 55,	R5. 6	R	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	27 29 33 35 41 44 45 59 38	85	R25 35 35 45 54	II p n n e 4 a n n e. Bce cong				V
	 	- 71 7							,	,									

NIKOLAYENKO, W.S.

Semigraphical method of calculating low-frequency transistor amplifiers. Radiotekhnika 15 no.7:51-59 J1 *60.

(MIRA 13:7)

(Transistor amplifiers)

FIERS WITH NINTERCASCADE CONNECTION AND THEIR APPLICATION IN MEASURING EQUIPMENT." LENINGRAD, 1961. (MIN OF HIGHER AND SEC SPEC ED RSFSR. LENINGRAD INST OF AVIATION INSTRUMENT HAVELD.). (KL-DV, 11-61, 221).

-172-

S/146/61/004/006/003/020 D249/D301

AUTHORS:

Nikolayenko, N. S. and Fedotov, V. P.

TITLE:

Current converters with semiconductor triodes

PERIODICAL:

Izvestiya vysshikh uchebnykh zavedeniy. Priborostroy-

eniye, v. 4, no. 6, 1961, 17-25

TEXT: A general description is given of converters of small d.c. signals into a.c. signals by semiconductor triodes which is compiled from literature. Characteristics of the semiconductor triode as a converter, compensation of residual parameters and characteristics of the converter in amplifier circuits for direct current are considered. There are 6 figures and 17 references: 4 Sovietaloc and 13 non-Soviet-bloc. The 4 most recent references to the bloc and 13 non-Soviet-bloc. The 4 most recent references to the English-language publications read as follows: A. Gill, Transistor English-language publications read as follows: A. Gill, Transistor Switch design, Electronics, 1958, XII no. 49, 97; R. B. Hurley, Switch design, Electronics, less transistor circuits, Electr. Industry, no. Transistorized low-level choppers circuits, Electr. Industry, no. 12, 1956; B. T. Barber, L. S. Klivan, Servo Modulators - III, Semiconductor modulators, magnetic modulators, tabulated characters

card 1/2

27780 5/106/61/000/008/004/006 A095/A127

Nikolayenko, N. S.

TITLE:

Selecting transistorized amplifier circuits

PERIODICAL: Elektrosvyaz*, no. 8, 1961, 40-46

TEXT: Eight different transistorized amplifier circuits (with capacitive, transformer or direct coupling) are analyzed, and their power amplification factor is calculated. The grapho-analytical method is used [Ref. 2: N. S. Nikolayenko. "Grafoanaliticheskiy metod rascheta nizkoehastotnykh usiliteley na poluprovodníkovykh triodakh" (Grapho-analytical method for calculating 1-f transistorized amplifiers), Radiotekhnika, 1960, no. 7], i.e. the transistor parameters are taken from their characteristics:

$$K_i = f_1(I_k)$$
 at $R_e = const.$

$$R_{inp} = f_2(I_k)$$
 at $R_e = const.$

In all the analyzed circuits, germanium transistors of the "P13", "P13A" and "P9A" types are used. A one-stage amplifier with a capacitive input is shown. Calculating the power transmission coefficient, first from the signal generator

Card 1/5

27780 **s/106/61/**000/008/004/006 A055/A127

Selecting transistorized amplifier pircuits

to the divider resistance, then from the divider resistance to the input resistance of the stage, the author finally obtains the total power transmission coefficient:

$$m = \frac{r_{gen}}{r_{gen} + 2*} \frac{R_{div}}{\sqrt{(R_{div} + R_{inp})^2 + (\frac{R_{1}}{\omega c_2})^2}}$$
 (5)

where

$$R_{\text{div}} = \frac{R_1 R_2}{R_1 + R_2}$$
 (3)

and

$$R_{\text{div}} = \frac{R_{1} R_{2}}{R_{1} + R_{2}}$$

$$Z^{*} = \frac{R_{\text{div}} \sqrt{R_{\text{inp}}^{2} + (\frac{K_{1}}{\omega c_{2}})^{2}}}{\sqrt{(R_{\text{div}} + R_{\text{inp}})^{2} + (\frac{K_{1}}{\omega c_{2}})^{2}}}$$
(2)

 $R_{\mbox{inp}}$ being the transistor input resistance. The power amplification factor of the stage with common emitter point is:

Card 2/5

27780 S/106/61/000/008/004/006 A055/A12

Selecting transistorized amplifier compassions

$$K_{p} = \frac{k_{1}^{2} Z_{1}}{Z_{inp}} = \frac{k_{1}^{2} Z_{1}}{\sqrt{R_{inp}^{2} + (\frac{k_{1}}{\omega C_{2}})^{2}}}$$
 (6)

and the power amplification factor of the circuit:

$$K_{p_{1}} = \frac{r_{gen} R_{div}}{(r_{gen} + Z^{*}) \sqrt{(R_{div} + R_{inp})^{2} + (\frac{k_{1}}{\omega C_{2}})^{2}}} \cdot \frac{k_{1}^{2} Z_{1}}{\sqrt{R_{inp}^{2} + (\frac{k_{1}}{\omega C_{2}})^{2}}}$$
(7)

Under optimum conditions and with optimum parameters, the average gain is 30 db with an input resistance of 1 kilohm approximately. Then a one-stage amplifier with transformer coupling is shown. The power amplification factor of the circuit is here:

$$K_{n_2} = \frac{\eta_{mp}}{2} = \frac{k_1^2 Z_1}{R_{inp}}$$
 (11)

where η_{mp} is the efficiency of the transformer. The gain reaches 35 db. The

Card 3/5

27780 S/106/61/000/008/004/006 A055/A127

Selecting transistorized amplifier circuits

input resistance can vary, depending on the parameters of the input transformer. Another figure shows a two-stage amplifier with direct coupling and with p-n-r type transistors. The temperature stabilization conditions were examined by the author in another article [Ref.1: "Usilitel" na poluprovednikovykh triodakh s neposredstvennoy svyaz'yu" ("Transistorized amplifier with direct coupling"), Radiotekhnika, 1958, v. 13, no. 2]. The power amplification factor of this circuit is:

 $K_{p3} = \frac{k_{11}^{2} k_{12}^{2} r_{gen} R_{div} R_{1}^{2} Z_{1}}{(r_{gen} + Z^{*}) \left[\sqrt{(R_{div} + R_{inpl})^{2} + (\frac{k_{11}}{\omega C_{2}})^{2}} \right] x (R_{y} + k_{12}Z_{1})^{2} \sqrt{R_{inpl}^{2} + (\frac{k_{1}}{\omega C_{2}})^{2}}}$

The gain is of the order of 40 dt (with an input resistance of about 1 kilohm). The author examines next the five following circuits and calculates the power amplification factor for each of these circuits: 1) A two-stage amplifier with direct interstage coupling (symmetrical transistor types being used). The gain is here of the order of 50 db. The input resistance varies within wide limits. 2) A two-stage amplifier with transformer coupling. The average gain is here 60 db. 3) A three-stage amplifier with direct interstage coupling, using the

Card 4/5

27780 S/106/61/000/008/004/006 A055/A127

Selecting transistorized amplifier

same type of transistors. The gain is about equal to 75 db. 4) A three-stage amplifier with direct interstage coupling, using alternately transistors of different types. The average gain is, in this case, 85 db. 5) A five-stage amplifier with direct interstage coupling, using transistors of the same type. The gain, in this case, is usually of the order of 110 ; 115 db. There are 8 figures and 7 Soviet-bloc references.

SUBMITTED: May 3, 1960

[Abstracter's note: The following subscripts are translated in text and formulae: gen (generator) stands for Γ and ι ; l (load) stands for H; s (signal) stands for C; div (divider) stands for ∂ ; inp stands for $\partial \Gamma$.

#

Card 5/5

5/146/62/005/001/003/011 D234/D302

AUTHORS:

Nikolayenko, N.S. and redotov, v.P.

TITLE:

A semiconductor triode in the regime of transformation

of small d.c. into a.c.

PERIODICAL:

Izvestiya vysshikh uchebnykh zavedeniy. Priborostroyeniye,

v. 5, no. 1, 1962, 16-26

TEXT: The authors determine the residual voltage and current and the resistance between the emitter and collector for the case stated and give a relation between these parameters and the current amplification factor and inverse transition currents. Temperature dependence of the parameters in a transformation regime is analyzed. Theoretical and experimental values of several dependences are compared. It is concluded that comparatively good stabilization in a wide temperature range is only possible when the load resistance is of the order of several hundreds of ohms or less. For high resistances silicone triodes are recommended. There are 5 figures and 8 references: 5 Soviet-bloc and 3 non-Soviet-bloc. The references

Card 1/2

S/146/62/005/001/003/011 D234/D302

A semiconductor triode in ...

to the English-language publications read as follows: J.J.S. Ebers, and J.J.L. Moll, Large-signal behaviour of junction transistors. Proc. I.K.E, 1954, Dec. 142.; E. Steele, Theory of a p-n*p diffused junction transistors. PIRE, 1952, 40, 1424.

ASSOCIATION: Leningradskiy elektrotekhnicheskiy institut im. V.1. Ul'yano-va (Lenina) (Leningrad Institute of Electrical Engineering im. v.I. Ul'-yanov (Lenin))

SUBMITTED: Feb

February 27, 1961

Card 2/2

NIKOLAYENKO, N. S.

Standard semiconductor amplifier for automatic potentiometers and bridges. Priborostroenie no.10:9-11 0 162.

(MIRA 15:10)

sansari de para santa de la compania de la compania

(Transistor amplifiers)

NIKOLAYENKO, N.S.; FEDOTOV, V.P.

Measuring transistorized d.c. converter and its use.
Priborostroenie no.11:18-20 N '62. (MIRA 15:12)

(Electric current converters)

s/115/63/000/001/014/017 E192/E382

9.2520

Nikolayenko, N.S.

Design principles of "hybrid" amplifiers AUTHOR:

Izmeritel'naya tekhnika, no. 1, 1963, 42 - 43 TITLE: PERIODICAL:

High input impedance (greater than 107 ohm) in a transistor amplifier can be achieved by preceding it with a vacuum tube amplifying stage. A possible circuit for such a "hybrid" amplifier is shown in the figure. The input tube is a directly heated sub-miniature pentode, type 1 1 175 with a heater of 1.2 V and 60 mA. The tube operates at an anode voltage of 15 V, a cathode current of 1.7 mA and grid bias of -0.1 V. The input tube is connected as a cathode-follower with a grid resistance of 2 MQ and $R_1 = 56 \Omega$, $R_2 = 3 k\Omega$; its input resistance is therefore $10^8~\Omega$ and output resistance 750 Ω . The output is connected directly to the base of the first transistor stage. The circuit shown in the figure employs transistors, type 179A (P9A) and has a gain of about 5000. There is 1 figure.

Card 1/2

S/146/63/006/001/001/014 D201/D308

AUTHORS: Nikolayenko, N. S. and Fedotov, V. P.

TITLE: Special features in the use of silicon transistors as d.c. to a.c. converters for small signals

PERIODICAL: Izvestiya vysshikh uchebnykh zavedeniy. Priborostroysniye, v. 6, no. 1, 1963, 19-26

TEXT: The authors snalyze germanium and silicon transistors from the point of view of their use as choppers in d.c. amplifiers and describe the methods of their selection and of the design of circuit components: A chopper circuit for a wide temperature range of operation, utilizing a silicon transistor with saturation voltage compensation is described. The theory and experimental investigation of the transistor characteristics show that, for small d.c. signal conversion, the silicon transistors give a better performance in the presence of a wide temperature range. They are much inferior, however, to germanium transistors where reproducibility, economy and simplicity of design are of importance. The use of silicon

Card 1/2

Special feat	ures in	S/1 D20	46/63/006/001, 1/ <i>0</i> 308	/001/014	
transistors (ing at high a ces having hi	should, therefore ambient temperatur igh internal resid	, be restrict	ed to converte	ers operat- i d.c. sour	•
ASSCOTATION:	Leningradksiy el Ul'yanova (Lenin Engineering im.	lektrotekhnich	eskiy institu		
UBMITTED:	November 25, 196	(1925年) (1946年) (1945年) (1945年) (1945年) (1945年) (1945年) (1945年)			

L 1026h=63 ACCESSION NE: AP3000562 S/0109/63/008/005/0807/0813

AUTHOR: Micolayenko, N. S.

44

TITLE: Operating conditions and amplification of compound-transistor circuits

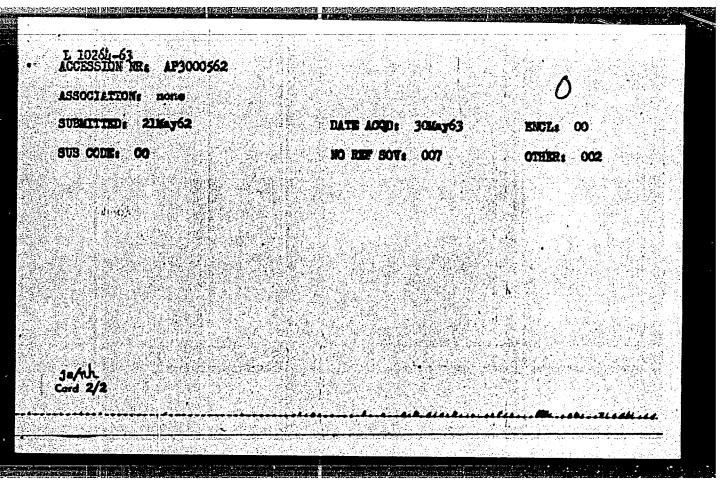
Sounce: Badiotekimika 1 elektronika, v. 8, me. 5, 1963, 807-813

TOPIC TACE: compound translator, Soviet translators

ABSTRACT: Effect of ambient temperature on the collector and emitter currents and load voltage is considered theoretically, and some experimental data is submitted. For a composite transistor of two P26 types, this effect is insignificant in the 20-802 range. Current gain (148) and imput impedance (1,650 ohms) for the same compound transistor have been estimated and verified experimentally. It is indicated that for P105 type and a load of 1,000 ohms, the current gain is 240, power gain in 2,450 and imput impedance 19,400 ohms. The use of compound transistor in various circuits is evaluated, and a comperison with a 2-stage transistor amplifier is given. Orig. art. has: 37 equations, 6 figures, and 1 table.

	•																	
	7																	

"APPROVED FOR RELEASE: 07/19/2001 CIA-RDP86-00513R001137030008-8



NIKOLAYENKO, N.S.

Parametrical description of the control of the cont

Transistor stage with a composite feedback. Radiotekhnika 13 no.10:30-34 0 '63. (MIRA 16:12)

1. Deystwitel'nyy chlen Nauchno-tekhnicheskogo obshchestva radiotekhniki i elektrosvyazi im. A.S.Popova.

L 6739-65 AFETR/ESD(c)/ASD(u)-5/AFWL/ESD(t)/RAEM(t) ACCESSION NR: AP4044178 8/0119/64/000/008/0001/0003 AUTHOR: Nikolayenko, N. S. (Candidate of technical sciences) TITLE: Transistorized amplifiers supplied by a pulsating current SOURCE: Priborostroyeniye, no. 2, 1964, 1-3 TOPIC TAGS: amplifier, transistorized amplifier, single ended amplifier, push pull amplifier ABSTRACT: Power relations in a single-ended, pulsating-current-supplied, class B transistorized amplifier are analyzed. An efficiency of up to 95% is held possible for this mode of operation. The use of transistors in push-pull circuits of both (different ated-load and differentiated-supply) types is regarded as impractical because of the strict symmetry requirements of the circuit. A single-ended, tuned-load-circuit amplifier is recommended for practical application, such as measuring instruments, automatic devices, etc.; a commonard 1/2

L 6739-65			
ACCESSION N	R: AP4044178		0
collector circu	it is recommen	ded for supplying some	
gain in class B	or AB amplific	eation with pulsating-cur	notors. Calculation of the
by experiments	ampiniers, "T	he above calculation was has: 3 figures and 14 fo	nalytical methods used for s verified and corroborated
Bo名人性のでは、特別はおきのいるか。	항상하는 물 보다를 하면 가득 끝나니었다.		rmulas,
ASSOCIATION:	none		
SUBMITTED:	00		
			ENCL: 00
		기독 목표를 내용한 그는 아이 집에 집에서 가장하다. 아래가 이 가능한 속에 되게	かいしゅう としゅうがく いって だいしょうしゃ しゅうしゃ しゅうしゅう コーライン みっこうりょうしょすり
SUB CODE: E(NO REF SOV: 005	OTHER: 001
SUB CODE: E	3	NO REF SOV: 005	OTHER: 001
SUB CODE: E(NO REF SOV: 005	OTHER: 001
SUB CODE: E(NO REF SOV: 005	- OTHER: 001
SUB CODE: E		NO REF SOV: 005	OTHER: 001

ACCESSION NR: AT4040775

8/2657/64/000/011/0037/0054

AUTHOR: Nikolayenko, N. S.

TITLE: Analysis of feedback circuits for the stabilization of transistor amplifier operation

SOURCE: Poluprovodnikovy*ye pribory* i ikh primeneniye; sbornik statey, no. 11, 1964, 37-54

TOPIC TAGS: feedback, feedback circuit, semi-conductor device, amplifier, transistor amplifier, amplifier stabilization, negative feedback

ABSTRACT: The author notes that the operation of transistorized amplifiers with direct interstage coupling can be stabilized rather well within the temperature range determined by the working temperatures of the transistors. However, the spread in the values of the circuit/resistances used in the mass production of these amplifiers gives rise to deviations from the design values which may be quite considerable (even when using resistances with a tolerance of \pm 5%) and which may lead to impairment or complete loss of amplifier operability. If direct interstage coupling is employed, the stability of transistor amplifiers can be increased substantially by introducing parallel-type negative feedback circuits.

Card/3

中国的人名英格兰的英国英国英国英国英国英国英国英国英国英国英国英国英国英国英国英国英国英国

ACCESSION NR: AT4040775

Card 2/3

The author divides these circuits into the following classes: "collector - base" feedback; "collector - emitter" feedback" "emitter - base" feedback; and "emitter - emitter" feedback. Analysis shows that the use of the last two types is preferable, since do feedback from the collector leads to the necessity of inserting additional decoupling filters, lowers the gain of the stage and increases the current consumption in the circuitry. The present article, therefore, contains a comparative analysis of five possible cases of three-stage transistor amplifiers with circuitry containing negative feedback of the parallel type fed from the emitters of the subsequent stages. Possible versions of the circuitry of 3-stage amplifiers incorporating one or two feedback systems are studied. The author also derives expressions which make possible the analysis of the stability of the working modes of the amplifier in the event that the actual values of the resistances employed deviate from the rated values. Experimental material is presented which both confirms the accuracy of the analysis and indicates the degree of stability in the amplifier modes in the face of variations in ambient temperature. The use of the analytical expressions and the results of the comparative circuit analysis given in this paper will make it possible, in each individual instance involving transistor amplifier design, to employ the proper feedback circuits for the best stabilization of the working modes of the transistors. Orig. art. has: 4 tables, 6 figures and 69 formulas.

ACCESSION NR: AT4040775

ASSOCIATION: none

SUBMITTED: 00

SUB CODE: EC

Card 3/3

NO REF SOV: 002

ENCL: 00

OTHER: 000

NIKOLAYENKO, N.3.

Method for designing translator amplifiers with multiloop
feedback. Radiotekh. 1 elektron. 9 no.4:693-709 Ap '64.

(MIRA 17:7)

Talvidico anonivishi() s (Veression XIII Xevovisi

5/0108/64/019/010/0047/0055

AUTHOR: Nikolayenko, N. S. (Active member)

TITLE: Parallel feedback in transistorized amplifiers with direct coupling

between stages

SOURCE: Radiotekhnika, v. 19, no. 10, 1964, 47-55

TOPIC TAGS: transistorized amplifier, negative feedback transistorized

amplifier

ABSTRACT: Decoperating conditions in direct-coupled multistage amplifiers depend on the spread of values of the resistors used in the circuit. To overcome this shortcoming, a parallel dec feedback in one of the stages is suggested. Design formulas for Ge- and Si-transistor 2- and 3-stage amplifiers are developed; the effect of the parallel feedback on the amplifier gain is taken into account. It is found that amplifiers with a parallel-feedback loop from an even-

Card 1/2

L 19784-65

ACCESSION NR: AP4047813

stage common emitter to the base of the first transistor have the highest stability. Such amplifiers are least sensitive to transistor-parameter sproad, resistor offrating, and ambicamperature. Experimental corroboration is claimed (no data supplied). Orig. art. has: 4 figures and 72 formulas.

ASSOCIATION: Nauchno-tekhnicheskoye obshchestvo radiotekhniki i elektrosvyazi (Scientific and Technical Society of Radio Engineering and Electrocommunication)

SUBMITTED: 05Mar62

ENCL: 00

SUB CODE: EC NO REF SOV: 004

OTHER: 002

Card 2/2

PIROZHENKO, V.Kh., inzh.; LINCHEVSKIY, G.V., inzh.; NIKOLAYENKO, N.T., inzh.

Automatically controlled mine traction substation using transistors.

Gor. zhur. no.5:69-70 My '63. (MIRA 16:5)

1. Gosudarstvennyy institut po proyektirovaniyu po dobyche i obogashcheniyu rud, g. Krivoy Rog.
(Electric substations)

PIROZHENKO, V.Kh.; LINCHEVSKIY, G.V.; NIKOLAYENKO, N.T.

Automatic mine traction substation equipped with semiconductors. Avtom. 1 prib. no.4:10-13 0-D 163. (MIRA 16:12)

1. Krivorozhskiy gosudarstvennyy institut po proyektirovaniyu oborudovaniya po dobyche i obogashcheniyu rud.

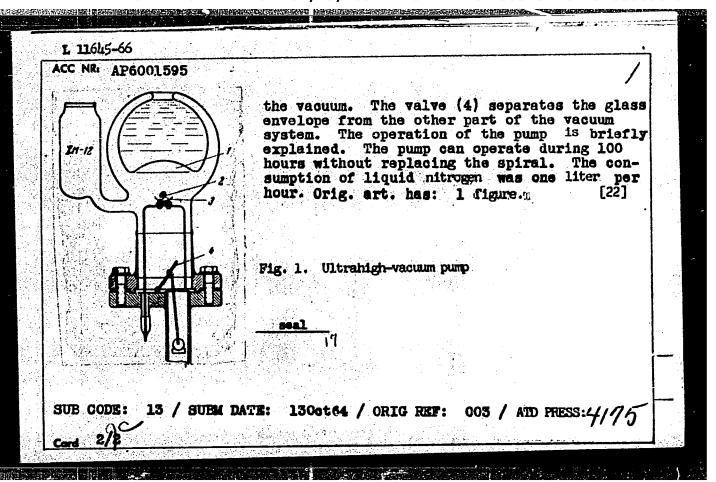
NIKOLAYENKO, N. V. Cand Agr Sci -- "Peculiarities of sugar beet species in various methods of cultivation under conditions of Chernovitskaya Oblast."

Odessa, 1960 (Min of Agr Ukssr. Odess Agr Inst). (KL, 1-61, 1)

-306-

V, KOLAYENKO, K. C. BLAGO NIKOLAYENKO, N.V.	OSKLANNAYA, Ya.V.; DAVYDOVSKIY, N.B.; LOSKUTOVA, Ye.A.; and
"The Ner	ryous Factor in Pathrgenesis of Engrotoxicusic."
report to be submitt	ted at the with Intl Guiter Conference, London, England, 1990 July 1997.

ENT(1)/ENT(m)/ENP(c)/ENP(v)/T/ENP(t)/ENP(k)/ENP(b)/ENP(b)/ENP(1)/ENA(b)/ L 11645-66 ACC NR: AP6001595 SOURCE CODE: UR/0120/65/000/006/0205/0206 Nikolayenko, O. K.; Bulgakov, Yu. V.; Tikhomirov, M. V. AUTHOR: Scientific-Research Physicochemical Institute, (Nauchno-issledovatel'skiy fiziko-khimicheskiy institut) Moscow 21,44,55 TITLE: A simple pump for obtaining an ultrahigh vacuum SOURCE: Pribory i tekhnika eksperimenta, no. 6, 1965, 205-206 TOPIC TAGS: high vacuum pump, vacuum technique ABSTRACT: A titanium nitrate pump is described. To It is made of glass and was designed for obtaining an ultrahigh vacuum of about 10-9 tor in a small limited space. The operation of the pump is based on the abnormal sorption of gases evaporated by titanium at temperatures lower than -170 C. A glass vacuum envelope with an interposed Kovar alloy connection was soldered to a flange made of stainless steel. A cross section of the pump is shown in Fig. 1. A ball-shaped surface (1) covered by a titanium film and cooled by liquid nitrogen (oxygen) serves as a pumping element. The electrically heated spiral (2) made of 0.7 mm molybdenum wire with a titanium coating is used as a titanium evaporator. The screen (3) prevents the discharge of titanium into Card 1/2



NIECLATURE, J. T.: "Pre-five of the form to refuse of constitution of the five of the state of the five of the fiv

AUTHOR:

Varnavskikh, A.P., Nikolayenko, P.T.

107-47-58-5-17/28

TITLE:

Two Experiments in Vibratory Votion (Dva opyta po kolebatel'-

nomu dvizheniyu/

PERIODICAL:

Fizika v shkole, 1958, Nr 5, pp 61-62 (43) F)

ABSTRACT:

Elastic oscillations can be well demonstrated with the aid of a vertical spring pendulum to obtain slowly dying oscillations with great periods (T = 2 - 3 sec). However, the influence of the weight of the oscillating body makes it impossible to show the change in the elastic force with respect to time. The device excludes the influence of weight. This is accomplished by turning the dial of the demonstration dynamometer until the needle is at zero. For the other experiment a detailed ex-

planation is given in the article.

There are 3 diagrams.

1 Vibrations--Analysis 2. Oscillations--Analysis

Card 1/1

1 08363-67

ACC NR. AR6028138

SOURCE CODE: UR/0058/66/000/005/D096/D096

21

AUTHOR: Nikolayenko, P. T.; Prorvin, A. I.

TITLE: . Investigation of intensity distribution in the wing of a Rayleigh line

SOURCE: Ref. zh. Fizika, Abs. 5D758

REF. SOURCE: Uch. zap. Kemerovsk. gos. ped. in-t, vyp. 9, 1965, 349-353

TOPIC TAGS: Rayleigh scattering, spectral line, line intensity, molecular spectrum, spectral distribution

ABSTRACT: The authors investigated the distribution of the intensity in the wing of a Rayleigh line in the frequency region 30 -- 120 cm⁻¹ for anisol, benzene, and 0xylol excited by the 4358 and 4047 % mercury lines. The experimental data are interpreted on the basis of the concept of two types of molecular motions causing the change in the frequency: 1) elastic oscillations relative to the equilibrium position; 2) Brownian rotary motion with a random-force power spectrum that depends on the frequency. For benzene and eight of its derivatives, the authors have determined the characteristic reorientation times, which have an order of magnitude 10-13 sec. V. Khartsiyev. [Translation of abstract]

SUB CODE: 20

nst Card 1//

L 27893-66 EWT(m)/EPF(c)	/EMP(j)/T RM SOURCE CODE: / UR/0286/65/000/016/0086/0086
ACC NR: AP5025044 AUTHORS: Mikolayanko, R. I.	Rusyantseva, L. V.; Polikanin, N. A. W.
ORG: none TITLE: A method for obtaini	ing polyphenylsiloxane resin. Class 39, No. 173956
SOURCE: Byulleten' izobrete	eniy i tovarnykh znakov, no. 16, 1965, 86
ABSTRACT: This Author Certi	nylsiloxane, toluol, furyl alcohol ificate presents a method for obtaining polyphenylsilox- myltrichlorsilane in a mixture of water and toluol. To in, furyl alcohol is added to the hydrolizing mixture.
	DATE: 09Jun62/ ORIG REF: 000/ OTH REF: 000

MIROLAYLENDO, S.S., inzh.; YES'KOV, A.G., Inzh.; CTTARIY. a.g., azh.;

MAKSHOCEK, A.A., Inzh.; WESELOV, Yu.a.,

Deepening the shaft of the Actintum blac. akht. str.

6 m. 126-25. Jl. 15.

1. Shod topromental acknowledge upravleminge floation of an analysis of maket produced (for Mikolayembo). 2. Krivorozlashi vitali da maket likrain on neuchnocisaledovatel'skogo institut granization i akhen datali na hitnego streitel'atva (for verlavi).

Raks neluh, Vesetty.

(Frivoy kog Basino-chaft sinala.

KONDON STATE OF STATE

NIKOLAYENKO, S. V.

4600. Nikolayenko, S. V. za uysokuyu kul'turu zemledehiya (rasskaz predserateyha kolkhoza im. voroshilova, glinyan. Rayona. lit zapis' f. zastavnogo.
I'vov, kn.-zhurn. ied., 1954. 30s. 20sm. (-eredovoy opytvsem kolkhoznikam.)
3, 000 ekz. 40k.-na ukr. yaz.-(54-57871) 338.1k(47.743)

SO: Letopis' Zhrunal' nykh Statey, Vol.7, 1949

NEVEROVSKAYA, V.O. [Nevierova'ka, V.O.]; NIKOLAYENKO, T.A. [Nykolaienko, T.O.];
ROTF, M.M.

New method for cutting garments. Leh.prom. no.4:45-46 O-D '62.
(MIRA 16:5)

1. Chernovitskaya trikotazhnaya fabrika No.l.
(Knit goods industry) (Garment cutting)

NIKOLAYENKO, V. A.

PHASE I BOOK EXPLOITATION

sov/6176

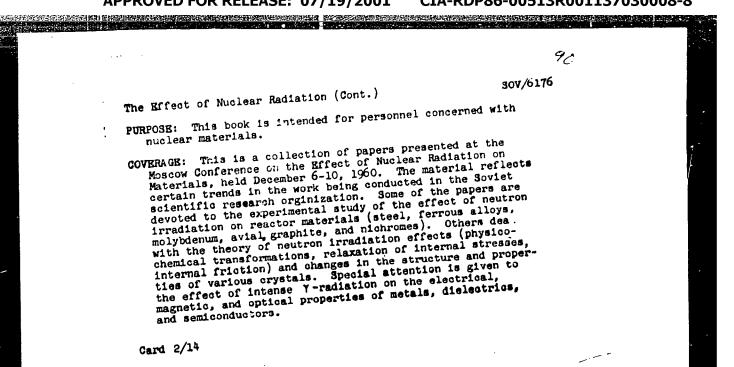
Konobeyevskiy, S. T., Corresponding Member, Academy of Sciences

Deystvive vadernykh izlucheniv na materialy (The Effect of Nuclear Radiation on Materials). Moscow, Izd-vo AN SSSR, 1962. 383 p. Errata slip inserted. 4000 copies printed.

Sponsoring Agency: Akademiya nauk SSSR. Otdeleniye tekini-cheskikh nauk; Otdeleniye fiziko-matematicheskikh nauk.

sp. Ed.: S. T. Konobeyevskiy; Deputy Resp. Ed.: S. A.
Adasinskiy; Editorial Board: P. L. Gruzin, G. V. Kurdyumov,
B. M. Levitskiy, V. S. Lyashenko (Deceased), Yu. A. Martynyuk,
Yu. I. Pokrovskiy, and N. F. Pravdyuk; Ed. of Publishing
House: M. G. Makarenko; Tech. Eds: T. V. Polyakova and
I. N. Dorokhina. I. N. Dorokhina.

card 1/14



,	5		
The Effect of Nuclear Radiation (Cont.) Batenin, I. V. V. A. Il'ina, V. K. Kritskaya, G. V. Kurdyumov, and B. V. Sharov. Investigation of the Effect of Neutron Irradiation on Thin Crystalline Structure and Properties of Irradiation on Thin Crystalline Structure and Properties of Metals and Alloys Annealed specimens (copper at 400°; iron and iron-nickel at 600°; iron-chromium and iron-tungsten at 650°; and chromium at 900°) were irradiated with neutron fluxes of chromium at 900°) were irradiated with neutron fluxes of chromium at 900° and ~10° n/om° at a temperature not exceeding 80° [C?]. Karpukhin, V. I., and V. A. Nikolayenko. Remote Controlled Installation for X-Ray Diffraction Analysis of Radioactive Specimens Levitskiy, B. M., and Yu. A. Martynyuk. Installation for X-Ray Examination of Righly Active Specimens Sharov, B. V.) I. V. Batenin, and A. N. Rudenko. X-Ray Unit for Structural Investigation of Radioactive Materials			
Card 8/14	,	. 1	
		:	
and the second			

The Effects of Nuclear Radiation (Cont.)	sov/ 6176
Pravdyuk, N. F., V. A. Nikolayenko, and V. I. Korpukhin Change in Lattice Parameters of Diamond and Silicon Ca During Irradiation	rbide 184
Abdullayev, G. B., and M. A. Talibi. On One Method of Cadmium Sulfide Photoresistors in Recording X- and Y-1 Dosimeter	Using ray 189
Konobeyevskiy, S. T., B. M. Levitskiy, L. D. Panteleyev Dubnovin, V. I. Kutaytsev, and V. N. Konev. X-Ray Exam tion of Transformations in Copper-Tin Alloy Under Neutr Irradiation	الما الدري
Levitskiy, B. M., and L. D. Panteleyev. X-Ray Examinat the Relaxation of Internal Microstresses in Cold-Worked Metals Under Neutron Irradiation	tion of i 209
Konobeyevskiy, S. T., N. F. Pravdyuk, Yu. I. Pokrovski; V. I. Vikhrov. Effect of Neutron Irradiation on Interfriction in Metals	y, and nal 219
Card 9/14	